

# SKM500GB17E4



SEMITRANS® 3

## IGBT4 Modules

### Evaluation Sample

### SKM500GB17E4

#### Target Data

#### Features\*

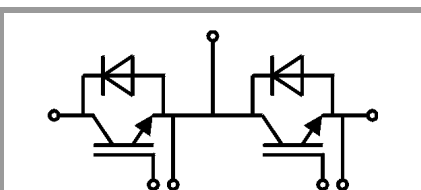
- IGBT4 = 4th generation medium fast trench IGBT (Infineon)
- CAL4 = Soft switching 4th generation CAL-Diode
- Insulated copper baseplate using DBC Technology (Direct Copper Bonding)
- With integrated Gate resistor
- For switching frequencies up to 8kHz
- UL recognized, file no. E63532

#### Typical Applications

- AC inverter drives
- UPS
- Electronic welders
- Wind power
- Public transport

#### Remarks

- Case temperature limited to  $T_c = 125^\circ\text{C}$  max.
- Recommended  $T_{op} = -40 \dots +150^\circ\text{C}$
- Product reliability results valid for  $T_j = 150^\circ\text{C}$



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Absolute Maximum Ratings				
Symbol	Conditions	Values	Unit	
<b>IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	1700	V	
$I_C$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	737	A
		$T_c = 80^\circ\text{C}$	565	A
$I_{Cnom}$		500	A	
$I_{CRM}$		1500	A	
$V_{GES}$		-20 ... 20	V	
$t_{psc}$	$V_{CC} = 1000\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1700\text{ V}$	$T_j = 150^\circ\text{C}$	10	$\mu\text{s}$
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Inverse diode</b>				
$V_{RRM}$	$T_j = 25^\circ\text{C}$	1700	V	
$I_F$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	546	A
		$T_c = 80^\circ\text{C}$	401	A
$I_{FRM}$		1000	A	
$I_{FSM}$	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	2880	A	
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Module</b>				
$I_{t(RMS)}$		500	A	
$T_{stg}$	module without TIM	-40 ... 125	$^\circ\text{C}$	
$V_{isol}$	AC sinus 50 Hz, $t = 1\text{ min}$	4000	V	

Characteristics						
Symbol	Conditions	min.	typ.	max.	Unit	
<b>IGBT</b>						
$V_{CE(sat)}$	$I_C = 500\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.90	2.20	V	
		$T_j = 150^\circ\text{C}$	2.45	2.80	V	
$V_{CE0}$	chipelevel	$T_j = 25^\circ\text{C}$	1.00	1.10	V	
		$T_j = 150^\circ\text{C}$	0.90	1.00	V	
$r_{CE}$	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.80	2.2	$\text{m}\Omega$	
		$T_j = 150^\circ\text{C}$	3.1	3.6	$\text{m}\Omega$	
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 20\text{ mA}$	5.2	5.8	6.4	V	
$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = 1700\text{ V}, T_j = 25^\circ\text{C}$			5	mA	
$C_{ies}$	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	40.4		nF	
$C_{oes}$		$f = 1\text{ MHz}$	1.60		nF	
$C_{res}$		$f = 1\text{ MHz}$	1.48		nF	
$Q_G$	$V_{GE} = -8\text{ V} \dots +15\text{ V}$	4000		nC		
$R_{Gint}$	$T_j = 25^\circ\text{C}$	1.0		$\Omega$		
$t_{d(on)}$	$V_{CC} = 1200\text{ V}$ $I_C = 500\text{ A}$	$T_j = 150^\circ\text{C}$	190		ns	
$t_r$	$V_{GE} = +15/-15\text{ V}$	$T_j = 150^\circ\text{C}$	60		ns	
$E_{on}$	$R_{G on} = 2\ \Omega$	$T_j = 150^\circ\text{C}$	160		mJ	
$t_{d(off)}$	$R_{G off} = 1\ \Omega$	$T_j = 150^\circ\text{C}$	760		ns	
$t_f$	$di/dt_{on} = 10700\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	160		ns	
$E_{off}$	$di/dt_{off} = 2500\text{ A}/\mu\text{s}$ $dv/dt = 3900\text{ V}/\mu\text{s}$ $L_s = 25\text{ nH}$	$T_j = 150^\circ\text{C}$	205		mJ	
$R_{th(j-c)}$	per IGBT			0.053	K/W	
$R_{th(c-s)}$	per IGBT ( $\lambda_{grease} = 0.81\text{ W}/(\text{m}^2\text{K})$ )			0.032	K/W	



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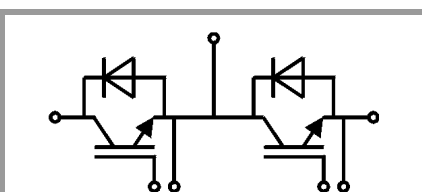
#### Typical Applications

- AC inverter drives
- UPS
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- Wind power
- Public transport

#### Remarks

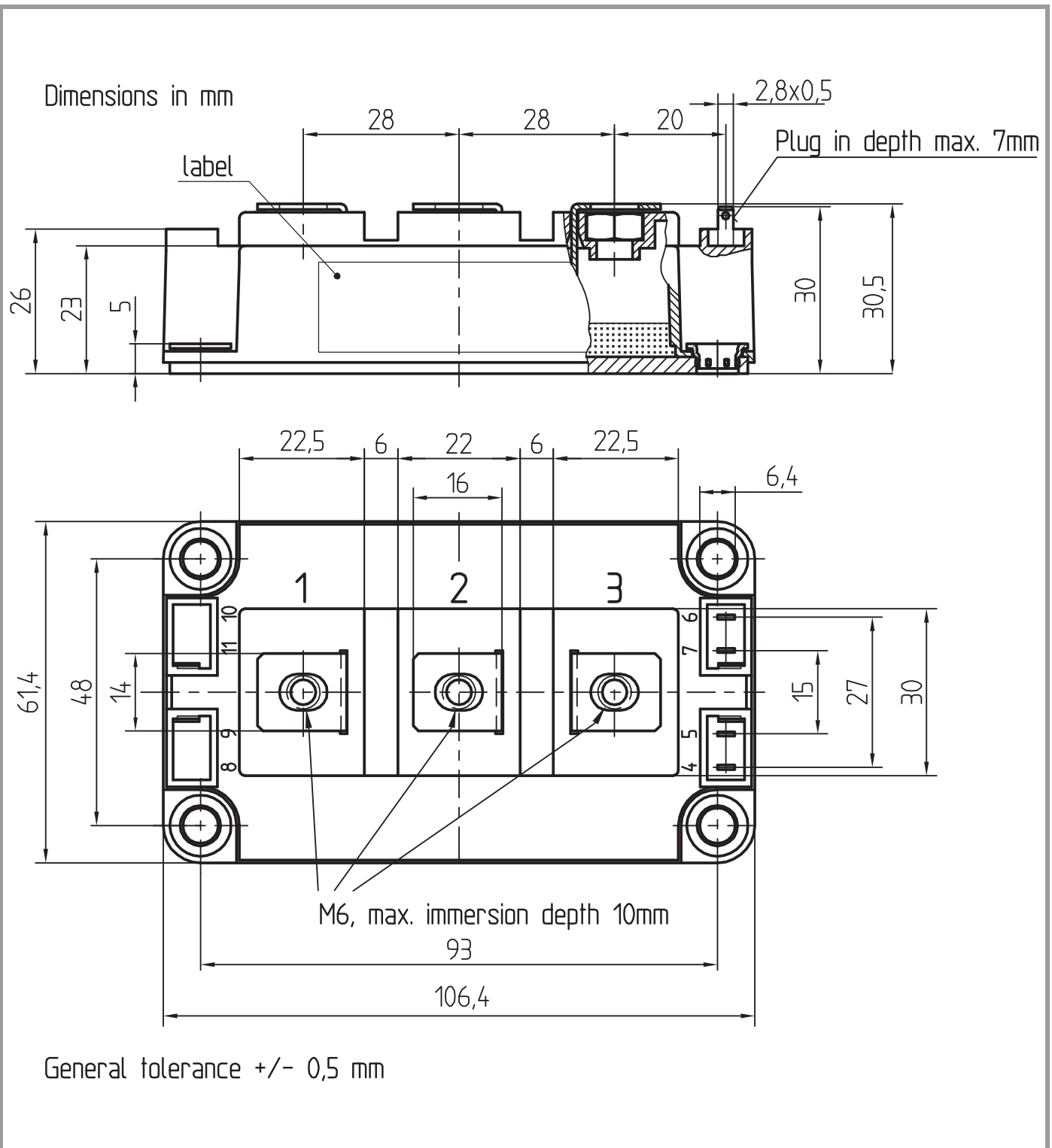
- Case temperature limited to  $T_c = 125^\circ\text{C}$  max.
- Recommended  $T_{op} = -40 \dots +150^\circ\text{C}$
- Product reliability results valid for  $T_j = 150^\circ\text{C}$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Inverse diode</b>						
$V_F = V_{EC}$	$I_F = 500\text{ A}$ $V_{GE} = 0\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$		1.96	2.35	V
		$T_j = 150^\circ\text{C}$		2.08	2.49	V
$V_{F0}$	chipelevel	$T_j = 25^\circ\text{C}$		1.32	1.56	V
		$T_j = 150^\circ\text{C}$		1.08	1.22	V
$r_F$	chipelevel	$T_j = 25^\circ\text{C}$		1.28	1.58	mΩ
		$T_j = 150^\circ\text{C}$		2.0	2.5	mΩ
$I_{RRM}$	$I_F = 500\text{ A}$	$T_j = 150^\circ\text{C}$		670		A
$Q_{rr}$	$di/dt_{off} = 8850\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		170		μC
$E_{rr}$	$V_{GE} = -15\text{ V}$ $V_{CC} = 1200\text{ V}$	$T_j = 150^\circ\text{C}$		130		mJ
$R_{th(j-c)}$	per diode				0.11	K/W
$R_{th(c-s)}$	per diode ( $\lambda_{grease}=0.81\text{ W}/(\text{m}^2\text{K})$ )			0.039		K/W
<b>Module</b>						
$L_{CE}$				15		nH
$R_{CC+EE}$	measured per switch	$T_c = 25^\circ\text{C}$		0.55		mΩ
		$T_c = 125^\circ\text{C}$		0.85		mΩ
$R_{th(c-s)1}$	calculated without thermal coupling ( $\lambda_{grease}=0.81\text{ W}/(\text{m}^2\text{K})$ )			0.0088		K/W
	including thermal coupling, $T_s$ underneath module ( $\lambda_{grease}=0.81\text{ W}/(\text{m}^2\text{K})$ )			0.014		K/W
$M_s$	to heat sink M6		3		5	Nm
$M_t$	to terminals M6		2.5		5	Nm
				-		Nm
w					325	g

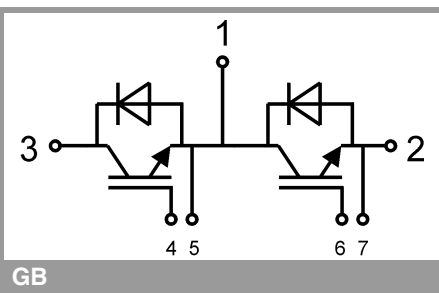


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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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